

FIG. 1

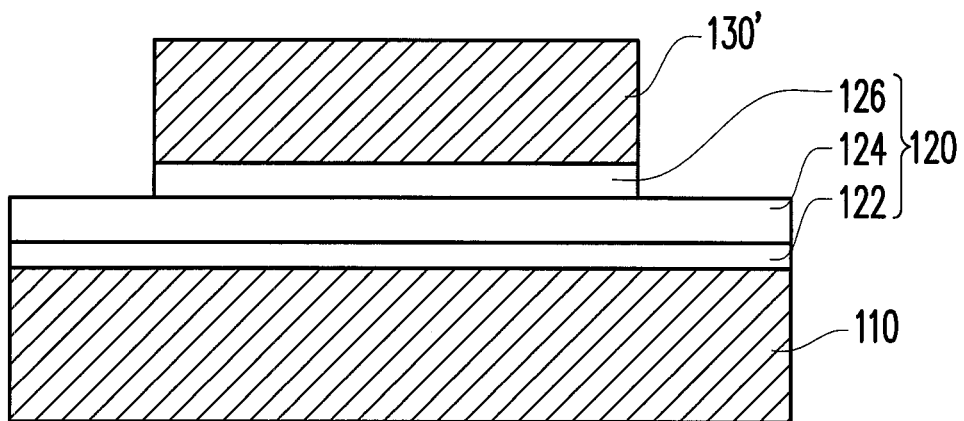


FIG. 2

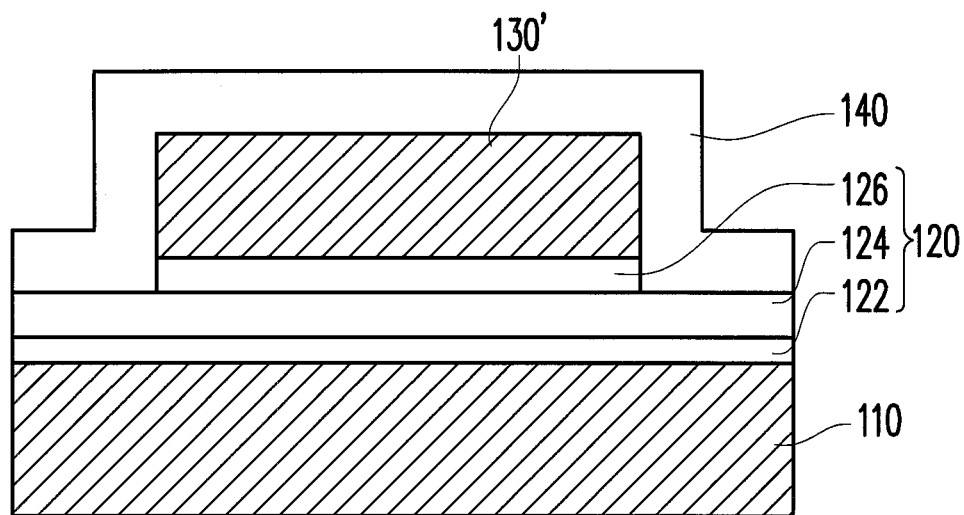


FIG. 3

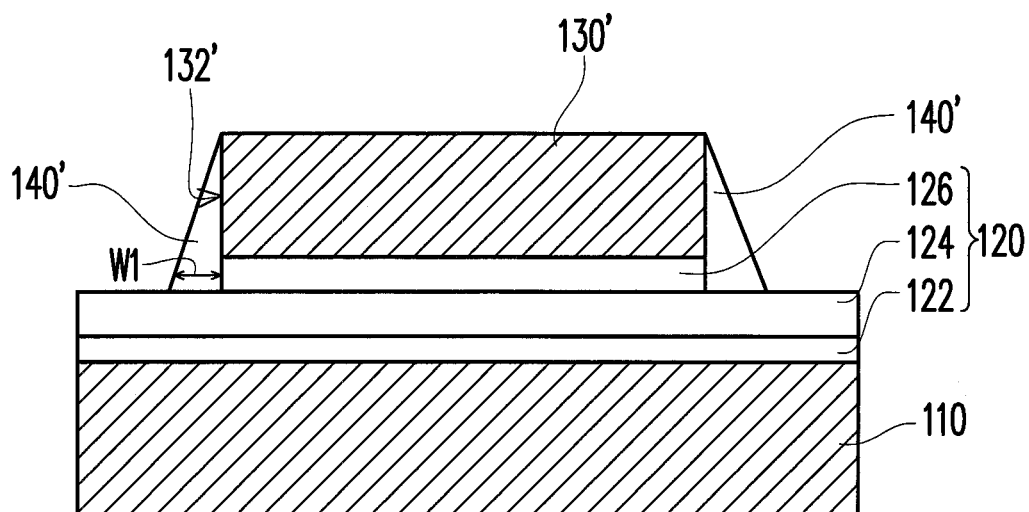


FIG. 4

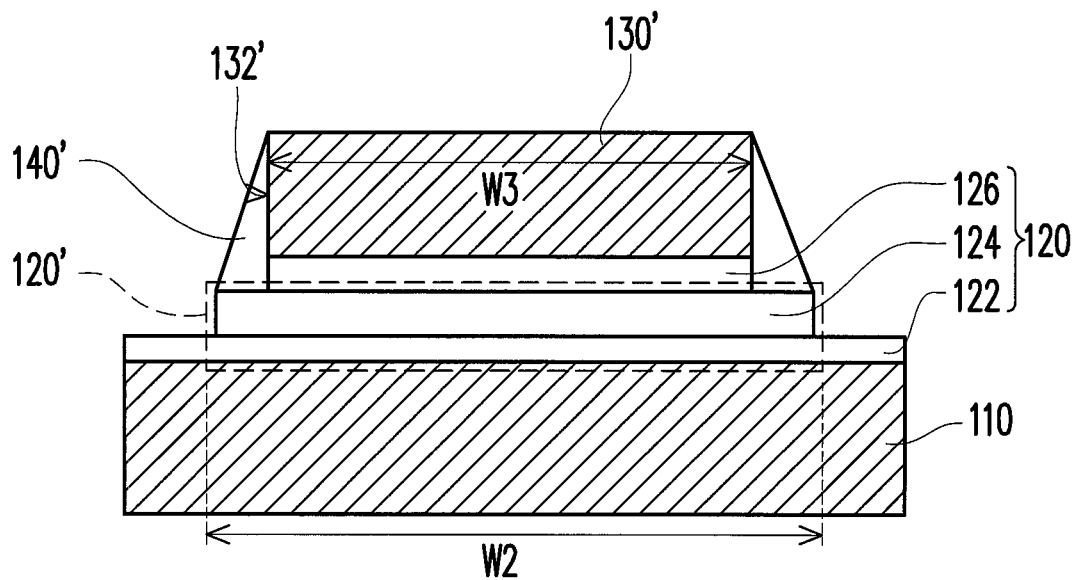


FIG. 5

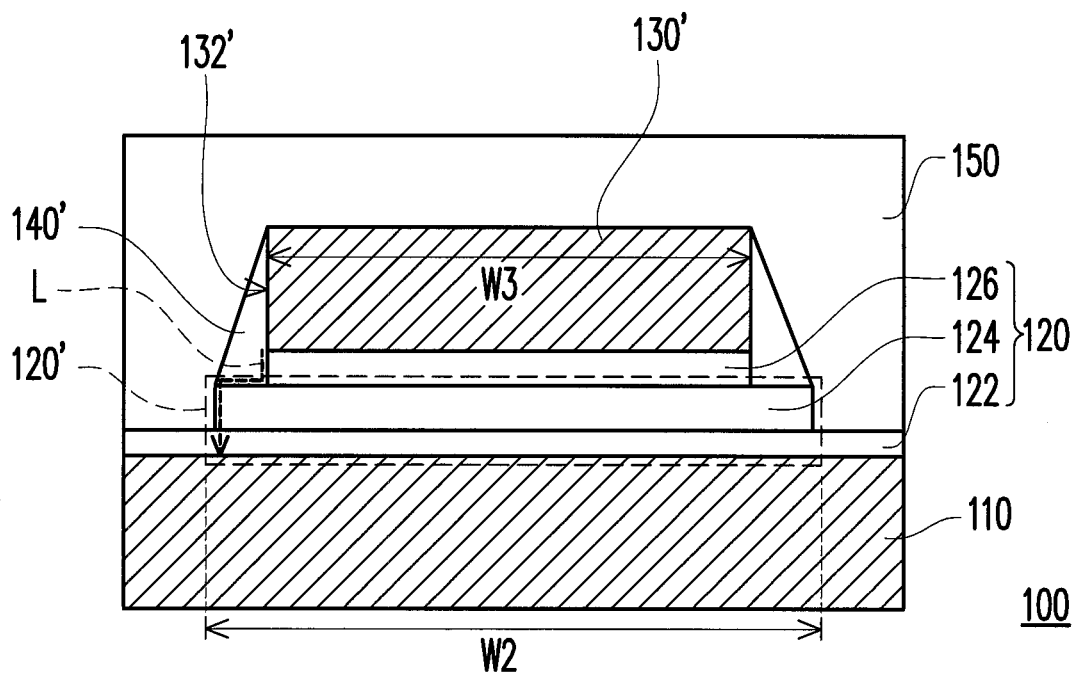


FIG. 6

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**METAL-INSULATION-METAL DEVICE****CROSS-REFERENCE TO RELATED APPLICATION**

This application claims the priority benefit of U.S. Provisional Application Ser. No. 61/470,508, filed on Apr. 1, 2011. The entirety of the above-mentioned patent application is hereby incorporated by reference herein and made a part of this specification.

**BACKGROUND OF THE INVENTION****1. Field of the Invention**

The invention generally relates to an electronic device and a manufacture method thereof and, in particular, to a metal-insulation-metal (MIM) device and a manufacture method thereof.

**2. Description of Related Art**

Nowadays, many electronic devices are usually integrated in a chip, especially for portable electronic apparatuses, for example, cellular phones, notebook personal computers (PCs), tablet PCs, personal digital assistants (PDAs), and digital cameras, and for some multi-function electronic apparatuses, for example, desktop PCs, DVD players, projectors, audio players, video game consoles, and multi-function washing machines. As a result, the volumes of the electronic apparatuses can be reduced and the response speed of the electronic apparatuses can be increased. Therefore, the electronic apparatuses can deal with more things for people, which greatly changes people's life style.

With the progress of the electronic technology, electronic devices are made smaller and smaller, which increases the number of the electronic devices in a unit area. In this way, a chip with the same area can achieve better performance, or the volume of the electronic apparatus can be reduced.

However, when the electronic devices are made smaller and smaller, many new problems occur. For example, when the volume of an MIM capacitor is reduced, the conductive path between two metal layers is shortened, so that a leakage current between the two metal layers is increased. As a result, the MIM capacitor is not suitable for operating in a high voltage.

**SUMMARY OF THE INVENTION**

Accordingly, the invention is directed to a manufacture method of a metal-insulation-metal (MIM) device, which reduces the leakage current in the MIM device.

The invention is directed to an MIM device, which has better performance.

An embodiment of the invention provides a manufacture method of a metal-insulation-metal (MIM) device. The manufacture method includes following steps. A first metal layer is provided. A first insulation layer is formed on the first metal layer. A second metal layer is formed on the first insulation layer. A part of the second metal layer is etched, wherein a remaining part of the second metal layer is not etched. A second insulation layer covering the remaining part of the second metal layer and the first insulation layer is formed. The second insulation layer is etched and a residual part of the second insulation layer is maintained on a side wall of the remaining part of the second metal layer. The first insulation layer is etched, wherein an intermediate part of the first insulation layer under the remaining part of the second metal layer and the residual part of the second insulation layer is not etched due to the remaining part of the second metal

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layer and the residual part of the second insulation layer serving as an etching barrier. A width of the intermediate part of the first insulation layer parallel to the first metal layer is greater than a width of the remaining part of the second metal layer parallel to the first metal layer.

Another embodiment of the invention provides an MIM device including a first metal layer, a first insulation layer, a second metal layer, and a second insulation layer. The first insulation layer is disposed on the first metal layer. The second metal layer is disposed on a part of the first insulation layer. The second insulation layer is disposed on a side wall of the second metal layer and on another part of the first insulation layer. A width of the first insulation layer under the second metal layer and the second insulation layer parallel to the first metal layer is greater than a width of the second metal layer parallel to the first metal layer.

In the manufacture method of the MIM device according to the embodiment of the invention, since the residual part of the second insulation layer is maintained on a side wall of the remaining part of the second metal layer, and since the width of the intermediate part of the first insulation layer parallel to the first metal layer is greater than the width of the remaining part of the second metal layer parallel to the first metal layer, the leakage current from the edge of the remaining part of the second metal layer is effectively reduced, thus increasing the performance of the MIM device. In the MIM device according to the embodiment of the invention, since the second insulation layer is disposed on a side wall of the second metal layer, and since the width of the first insulation layer under the second metal layer and the second insulation layer parallel to the first metal layer is greater than the width of the second metal layer parallel to the first metal layer, the leakage current from the edge of the second metal layer is effectively reduced, thus increasing the performance of the MIM device.

**BRIEF DESCRIPTION OF THE DRAWINGS**

The accompanying drawings are included to provide a further understanding of the invention, and are incorporated in and constitute a part of this specification. The drawings illustrate embodiments of the invention and, together with the description, serve to explain the principles of the invention.

FIGS. 1 through 6 are schematic cross-sectional views showing steps of a manufacture method of an MIM device according to an embodiment of the invention.

**DESCRIPTION OF THE EMBODIMENTS**

Reference will now be made in detail to the preferred embodiments of the invention, examples of which are illustrated in the accompanying drawings. Wherever possible, the same reference numbers are used in the drawings and the description to refer to the same or like parts.

FIGS. 1 through 6 are schematic cross-sectional views showing steps of a manufacture method of an MIM device according to an embodiment of the invention. Referring to FIGS. 1 through 6, the manufacture method of the MIM device according to this embodiment includes following steps. First, referring to FIG. 1, a first metal layer 110 is provided. For example, the first metal layer 110 is formed on a substrate, such as a silicon substrate. Specifically, the first metal layer 110 may be deposited on the substrate by physical vapor deposition (PVD) or chemical vapour deposition (CVD). In this embodiment, the first metal layer 110 is an electrically conductive layer. Then, a first insulation layer 120 (i.e. a dielectric layer) is formed on the first metal layer 110. In this embodiment, the first insulation layer 120 includes a

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silicon dioxide sub-layer **122**, a silicon nitride sub-layer **124**, and a silicon dioxide sub-layer **126** formed on the first metal layer **110** in sequence. However, in another embodiment, the first insulation layer **120** may also be a single insulation layer. The first insulation layer **120** may be deposited on the first metal layer **110** by PVD or CVD. After that, a second metal layer **130** is formed on the first insulation layer **120**. The second metal layer **130** may be deposited on the first insulation layer **120** by PVD or CVD. In this embodiment, the material of the second metal layer **130** includes aluminium, titanium nitride, or the combination thereof.

Next, referring to FIG. 2, a part of the second metal layer **130** is etched, wherein a remaining part **130'** of the second metal layer **130** is not etched. In this embodiment, the etching of the part of the second metal layer **130** may be performed by using a mask, for example, by using photolithography. In this embodiment, after etching the part of the second metal layer **130**, a top portion of the first insulation layer **120** not covered by the remaining part **130'** of the second metal layer **130** is over-etched. For example, a part of the silicon dioxide sub-layer **126** is etched.

Afterwards, referring to FIG. 3, a second insulation layer **140** covering the remaining part **130'** of the second metal layer **130** and the first insulation layer **120** is formed. For example, the second insulation layer **140** is deposited by PVD or CVD. In this embodiment, the second insulation layer **140** is, for example, a silicon dioxide layer. However, in another embodiment, the material of the second insulation layer **140** may be another appropriate insulation material. In this embodiment, the step of forming the second insulation layer **140** is, for example, blanket formation of the second insulation layer **140** on the remaining part **130'** of the second metal layer **130** and the first insulation layer **120**.

Then, referring to FIG. 4, the second insulation layer **140** is etched and a residual part **140'** of the second insulation layer **140** is maintained on a side wall **132'** of the remaining part **130'** of the second metal layer **130**. In this embodiment, the step of etching the second insulation layer **140** and maintaining the residual part **140'** of the second insulation layer **140** is a blanket etching (i.e. not using a mask), and the residual part **140'** of the second insulation layer **140** is naturally formed after the blanket etching. In this embodiment, the width **W1** of the residual part **140'** of the second insulation layer **140** parallel to the first metal layer **110** gradually decreases from a side of the residual part **140'** close to the first metal layer **110** to another side of the residual part **140'** away from the first metal layer **110**, and this phenomenon is naturally generated after the blanket etching.

Next, referring to FIG. 5, the first insulation layer **120** is etched, wherein an intermediate part **120'** of the first insulation layer **120** under the remaining part **130'** of the second metal layer **130** and the residual part **140'** of the second insulation layer **140** is not etched due to the remaining part **130'** of the second metal layer **130** and the residual part **140'** of the second insulation layer **140** serving as an etching barrier for resisting the etching of the first insulation layer **120**. The width **W2** of the intermediate part **120'** of the first insulation layer **120** parallel to the first metal layer **110** is greater than the width **W3** of the remaining part **130'** of the second metal layer **130** parallel to the first metal layer **110**.

In this embodiment, the manufacture method may further include forming a third insulation layer **150** (i.e. a dielectric layer) covering the first metal layer **110**, the intermediate part **120'** of the first insulation layer **120**, the residual part **140'** of the second insulation layer **140** and the remaining part **130'** of the second metal layer **130**, and an MIM device **100** is formed. In this

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way, another electronic device can be formed above the MIM device **100**. In this embodiment, the MIM device **100** is, for example, an MIM capacitor.

In the manufacture method of the MIM device **100** according to this embodiment, since the residual part **140'** of the second insulation layer **140** is maintained on the side wall **132'** of the remaining part **130'** of the second metal layer **130**, and since the width **W2** of the intermediate part **120'** of the first insulation layer **120** parallel to the first metal layer **110** is greater than the width **W3** of the remaining part **130'** of the second metal layer **130** parallel to the first metal layer **110**, the leakage current from the edge of the remaining part **130'** of the second metal layer **130** is effectively reduced, thus increasing the performance of the MIM device **100**. As a result, the MIM device **100** may operate in a high voltage. Specifically, since the intermediate part **120'** of the first insulation layer **120** laterally protrudes from the remaining part **130'** of the second metal layer **130**, the length of the conductive path of the leakage current **L** is increased, which increases the resistance between the remaining part **130'** of the second metal layer **130** and the first metal layer **110**. As a result, the leakage current is effectively reduced, thus increasing the performance of the MIM device **100**.

The MIM device **100** of this embodiment includes a first metal layer **110**, a first insulation layer (i.e. the first insulation layer **120** shown in FIG. 6), a second metal layer (i.e. the remaining part **130'**), and a second insulation layer (i.e. the residual part **140'**). The first insulation layer **120** is disposed on the first metal layer **110**. The second metal layer (i.e. the remaining part **130'**) is disposed on a part of the first insulation layer (i.e. the first insulation layer **120** shown in FIG. 6). The second insulation layer (i.e. the residual part **140'**) is disposed on the side wall **132'** of the second metal layer (i.e. the remaining part **130'**) and on another part of the first insulation layer (i.e. the first insulation layer **120** shown in FIG. 6). The width **W2** of the first insulation layer under the second metal layer (i.e. the remaining part **130'**) and the second insulation layer (i.e. the residual part **140'**) parallel to the first metal layer **110** (i.e. the width **W2** of the intermediate part **120'** shown in FIG. 6) is greater than the width **W3** of the second metal layer (i.e. the remaining part **130'**) parallel to the first metal layer **110**. In this embodiment, the MIM device **100** further includes the third insulation layer **150**. The advantage and the effect of the MIM device **100** are stated hereinbefore, and are not repeated herein.

In the manufacture method of the MIM device according to the embodiment of the invention, since the residual part of the second insulation layer is maintained on a side wall of the remaining part of the second metal layer, and since the width of the intermediate part of the first insulation layer parallel to the first metal layer is greater than the width of the remaining part of the second metal layer parallel to the first metal layer, the leakage current from the edge of the remaining part of the second metal layer is effectively reduced, thus increasing the performance of the MIM device. In the MIM device according to the embodiment of the invention, since the second insulation layer is disposed on a side wall of the second metal layer, and since the width of the first insulation layer under the second metal layer and the second insulation layer parallel to the first metal layer is greater than the width of the second metal layer parallel to the first metal layer, the leakage current from the edge of the second metal layer is effectively reduced, thus increasing the performance of the MIM device.

It will be apparent to those skilled in the art that various modifications and variations can be made to the structure of the invention without departing from the scope or spirit of the invention. In view of the foregoing, it is intended that the

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invention cover modifications and variations of this invention provided they fall within the scope of the following claims and their equivalents.

What is claimed is:

1. A manufacture method of a metal-insulation-metal (MIM) device, comprising:
  - providing a first metal layer;
  - forming a first insulation layer on the first metal layer;
  - forming a second metal layer on the first insulation layer;
  - etching a part of the second metal layer, wherein a remain-  
ing part of the second metal layer is not etched;
  - forming a second insulation layer covering the remaining  
part of the second metal layer and the first insulation  
layer;
  - etching the second insulation layer and maintaining a  
residual part of the second insulation layer on a side wall  
of the remaining part of the second metal layer;
  - etching the first insulation layer after forming the residual  
part of the second insulation layer, wherein an interme-  
diate part of the first insulation layer under the remaining  
part of the second metal layer and the residual part of the  
second insulation layer is not etched due to the remain-  
ing part of the second metal layer and the residual part of  
the second insulation layer serving as an etching barrier,  
wherein a width of the intermediate part of the first  
insulation layer parallel to the first metal layer is greater

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than a width of the remaining part of the second metal layer parallel to the first metal layer.

2. The manufacture method according to claim 1 further comprising:

- Forming a third insulation layer covering the first metal layer, the intermediate part of the first insulation layer, the residual part of the second insulation layer and the remaining part of the second metal layer.

3. The manufacture method according to claim 1, wherein the step of etching the second insulation layer and maintaining the residual part of the second insulation layer is an anisotropic blanket etching to form the residual part of the second insulation layer.

4. The manufacture method according to claim 1, wherein the step of forming the second insulation layer is blanket formation of the second insulation layer on the remaining part of the second metal layer and the first insulation layer.

5. The manufacture method according to claim 1 further comprising:

- after etching the part of the second metal layer, over-etching a top portion of the first insulation layer not covered by the remaining part of the second metal layer.

6. The manufacture method according to claim 1, wherein the second insulation layer is a silicon dioxide layer.

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